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November 2013

FQP30N06

N-Channel QFET $^{\circledR}$ MOSFET 60 V, 30 A, 40 m Ω

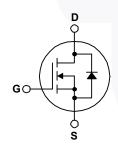
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 30 A, 60 V, $R_{DS(on)}$ = 40 m Ω (Max.) @ V_{GS} = 10 V, I_D = 15 A
- Low Gate Charge (Typ. 19 nC)
- · Low Crss (Typ. 40 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP30N06	Unit	
V_{DSS}	Drain-Source Voltage		60	V	
I _D	Drain Current - Continuous (T _C = 25°C)		30	Α	
	- Continuous (T _C = 100°C)		21.3	Α	
I _{DM}	Drain Current - Pulsed	(Note 1)	120	Α	
V _{GSS}	Gate-Source Voltage		± 25	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	280	mJ	
I _{AR}	Avalanche Current	(Note 1)	30	Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	7.9	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns	
P_{D}	Power Dissipation (T _C = 25°C)		79	W	
	- Derate above 25°C	0.53	W/°C		
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds	300	°C		

Thermal Characteristics

Symbol	Parameter	FQP30N06	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.90	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Marking and Ordering Information

Part Nu	ımber	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP30	0N06	FQP30N06	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.06		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V	-		1	μΑ
		V _{DS} = 48 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 15 A		0.031	0.04	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 25 V, I _D = 15 A		16		S
C _{iss}	ic Characteristics Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		725	945	pF
C _{oss}	Output Capacitance			270	350	pF
C _{rss}	Reverse Transfer Capacitance			40	52	pF
Switch	ing Characteristics		-1		l	
t _{d(on)}	ing Characteristics Turn-On Delay Time			10	30	ns
t _r	Turn-On Rise Time	$V_{DD} = 30 \text{ V, } I_{D} = 15 \text{ A,}$ $R_{G} = 25 \Omega$ (Note 4)		85	180	ns
t _{d(off)}	Turn-Off Delay Time			35	80	ns
t _f	Turn-Off Fall Time			40	90	ns
Qg	Total Gate Charge	V _{DS} = 48 V, I _D = 30 A,		19	25	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 10 \text{ V}$		5.4		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		8.5		nC
	Course Diede Characteristics and Mar	dimension Dations		1		
ار Drain-S	Source Diode Characteristics and Max Maximum Continuous Drain-Source Diode Forw				30	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				120	A
		V _{GS} = 0 V, I _S = 30 A			1.5	V
V_{SD}	Drain-Source Dioge Forward Voltage					
V _{SD}	Drain-Source Diode Forward Voltage Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = 30 \text{ A},$		45		ns

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = $360 \, \mu H$, $I_{AS} = 30 \, A$, $V_{DD} = 25 \, V$, $R_G = 25 \, \Omega$, starting $T_J = 25^{\circ}C$. 3. $I_{SD} \leq 30 \, A$, $di/dt \leq 300 \, A/\mu s$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^{\circ}C$. 4. Essentially Independent of Operating Temperature.

Typical Characteristics

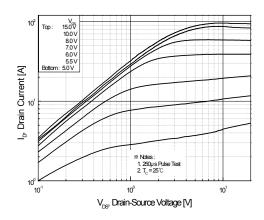


Figure 1. On-Region Characteristics

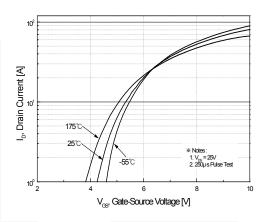


Figure 2. Transfer Characteristics

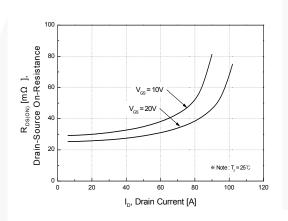


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

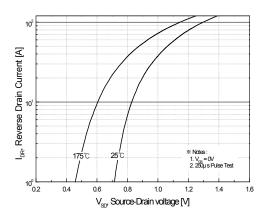


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

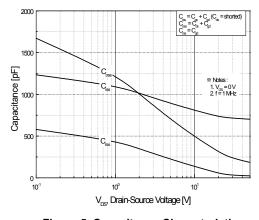


Figure 5. Capacitance Characteristics

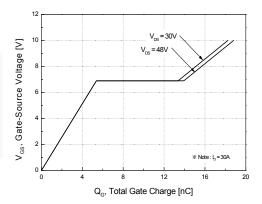


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

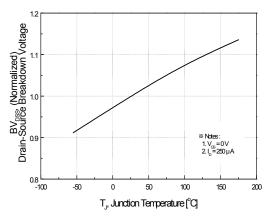


Figure 7. Breakdown Voltage Variation vs. Temperature

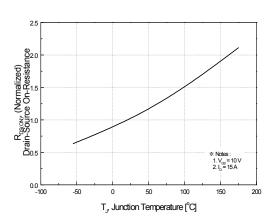


Figure 8. On-Resistance Variation vs. Temperature

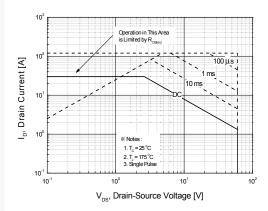


Figure 9. Maximum Safe Operating Area

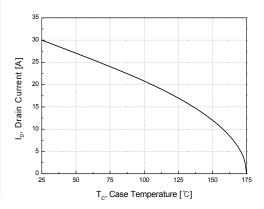


Figure 10. Maximum Drain Current vs. Case Temperature

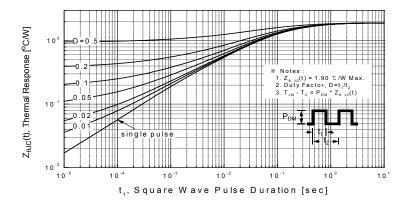


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

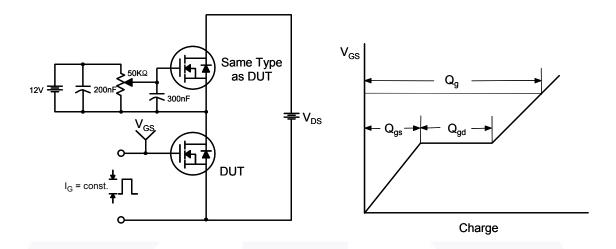


Figure 13. Resistive Switching Test Circuit & Waveforms

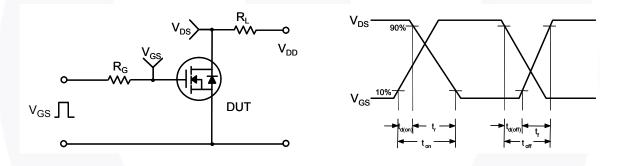
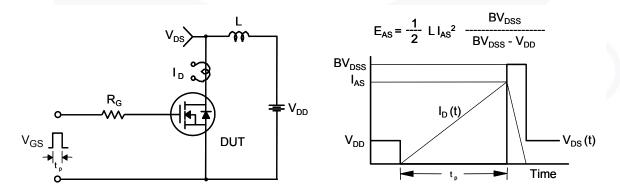


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



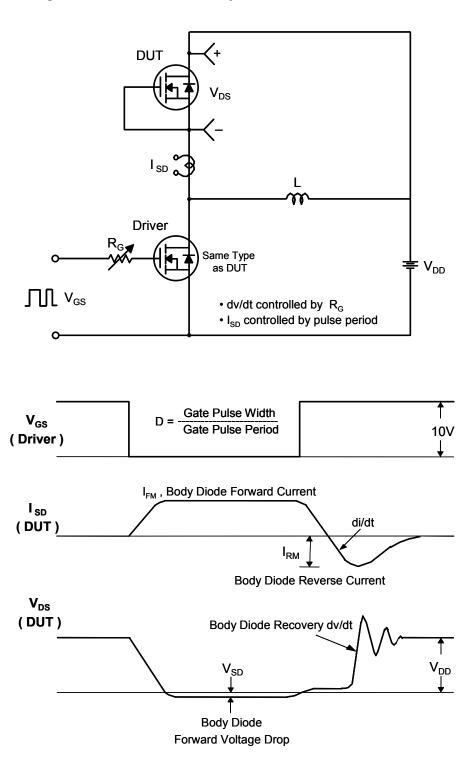
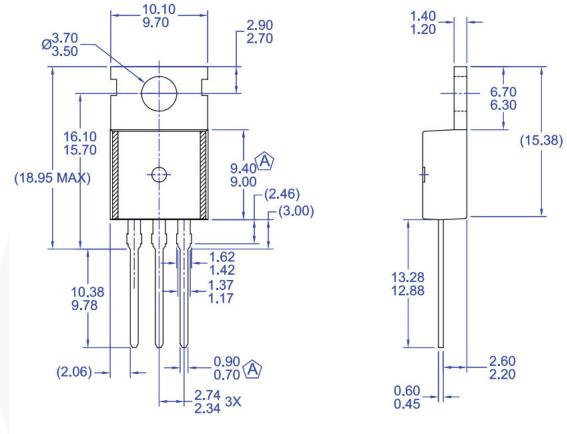


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



4.70 4.30 10.20 9.80

NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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